

X-ray Irradiation Results

Davide Braga, Mark Raymond

06 November 2014



Imperial College London



Science & Technology Facilities Council





NB: calculated for 3000 fb⁻¹ but with present Tracker

1e+17

1e+16

1e+15

1e+14

Fluence [cm⁻²]

https://twiki.cern.ch/twiki/bin/view/CMSPublic/ **BRILRadiationSimulation**

Total Ionizing Dose test at Diamond X-ray facility

- Molybdenum tube
- Wire-bonded CBC2 ("face-up")
- CBC2 always biased and operational during irradiation and annealing



Accelerated annealing





Irradiation cabinet

1st room-temp irradiation

1 chip irradiated to ~12 Mrads

no significant change to behaviour apart from:

current increase during early stages of irradiation ~ 1 Mrad decays away if stop irradiation effect disappears at higher dose levels

so not necessarily a problem, but

chips in HL-LHC will be cold - does that affect the behaviour? (the rate current decays away)

not clear what is going on and in what part of the chip (no separation between analogue/digital supplies)



Cooled setup results

VDDD and VDDA now supplied separately

current increase clearly confined to the digital rail (VDDD current)

but magnitude depends on whether <u>analog</u> stages biased or not



current saturates at around 800 krads stopped irradiation at this point

current still decays away with time constant ~1000 minutes, even at this cold temperature (c.f. ~200 minutes at ~30°)

NB: 850 rads/min is ~ 85x the worst case doserate at HL-LHC

More details in:

https://indico.cern.ch/event/332678/session/1/contribution/4/material/slides/0.pdf 5

Cooled setup results₃₀.

try a low dose-rate irradiation (new chip)

couldn't get continuous dose-rate low enough as that at HL-LHC*

but current plateaus at \sim 40 rads / min.



*30 Mrads / (10 years x 200 days x 24 hours x 60 mins) = ~10 rads/min

Summary so far

Cooled irradiation setup shows:

current increase confined to digital supply rail (VDDD)

but magnitude affected by values in analog bias registers (nominal or zero)

current is not "frozen in" by operation at low temperature

continuous annealing even at T= -15°C

→ should not be significant at HL-LHC dose-rates

Masked Irradiation

→ Demonstrated that increase in digital current is due to static leakage in SRAM memory at high-dose



Summary

- Excess static current due to drain-to-source leakage in pull-down nMOS of SRAM cell (non-ELT).
- Effect of analogue biasing on magnitude of the current explained by the biasing conditions during irradiation

- \rightarrow Origin of excess leakage and failure mechanisms understood
- → Effect should only be a problem at high-rate: should not cause problems for outer tracker (<30 Mrads over 10 years) but could cause problems at lower radii if CBC were to be used there
- \rightarrow Currently considering improved and alternative SRAM designs anyway

Higher dose rates

have now taken 1 chip to ~40 Mrads

~300 krad/hour

room temperature irradiation

power ~ static after initial digital transient

small shift in bandgap ~20 mV





Analogue bias voltages

pre-rad 10 Mrads 20 Mrads ~30 Mrads 41 Mrads



11

S-curves







Conclusions

- CBC2 shows expected radiation insensitivity to ~ 40 Mrads (40 Mrad limit dictated by availability of source)
- Irradiation to 40Mrad showed only a short-term increase in current which recovers completely even at T=-15°C annealing after a few hours
- Modules instrumented with CBC2s can be safely irradiated, at low dose it might be necessary to wait for a few hours before running the chips, at high-dose it should make no difference.